Single-photon emission mediated by single-electron tunneling in plasmonic nanojunctions

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Recent scanning tunnelling microscopy (STM) experiments reported single-molecule fluorescence induced by tunneling currents in the nanoplasmonic cavity formed by the STM tip and the substrate. The electric field of the cavity mode couples with the current-induced charge fluctuations of the molecule, allowing the excitation of the mode. We investigate theoretically this system for the experimentally relevant limit of large damping rate $\kappa$ for the cavity mode and arbitrary coupling strength to a single-electronic level. We find that for bias voltages close to the first inelastic threshold of photon emission, the emitted light displays anti-bunching behavior with vanishing second-order photon correlation function. At the same time, the current and the intensity of emitted light display Franck–Condon steps at multiples of the cavity frequency $\omega_c$ with a width controlled by $\kappa$ rather than the temperature $T$. For large bias voltages, we predict strong photon bunching of the order of the $\kappa/\Gamma$ where $\Gamma$ is the electronic tunneling rate. Our theory thus predicts that strong coupling to a single level allows current-driven non-classical light emission.

Electronic transport coupled to the field of an electromagnetic cavity can be realized in a wealth of different systems. This includes in the microwave range carbon-nanotubes [1–5], quantum-dots [6–9], and Josephson-junctions [10–12], or in the optical range, molecules in plasmonic nanocavities, formed by an STM tip with a substrate [13–22] and organic microwavities [23,25]. The reduction of the cavity volume $V$ allows to increase the zero-point quantum fluctuations of the electric field $E_{\text{zpm}} \sim V^{-1/2}$. This motivated optical studies of molecular two-level systems strongly coupled to the cavity field by the dipolar interaction $\Lambda_d \sim pE_{\text{zpm}}$, (with $p$ the molecule dipole moment). One of the goals of this effort is to reach $\Lambda_d$ larger than $\kappa$, which has been and remains challenging, despite recent achievements [20]. On the other side, the coupling of a cavity mode to the current-induced charge fluctuations of a single-electronic level is given by a monopolar coupling constant $\Lambda_m \sim e LE_{\text{zpm}}$ [24], with $L$ the typical extension of the transport region and $e$ the electronic charge. Since typically in a given system $eL \gg p$, the monopolar coupling constant is much larger than the dipolar one [27]. This probably contributed to the observation of values of $\Lambda_m$ larger than $\kappa$ in microwave cavities coupled to electronic transport [4,6,8,26] and even approaching the cavity resonating frequency $\omega_c$ ($h = 1$) [11,28,29]. Recent results in plasmonic cavities coupled to electronic transport [17,19,20] open thus the possibility to explore transport through a single electronic level in these structures. This is expected to reach much larger coupling constants than those currently observed for purely dipolar coupling, requiring further theoretical investigations.

The system presents strong analogies with electron-transport coupled to molecular vibrations. This has been investigated in different regimes, leading to the striking prediction of Franck–Condon blockade [30,32] and its observation [33,34]. However, there are important differences: The first is the low quality factor of plasmonic cavities, which is typically of the order of 10 [26]. The second, and more interesting, is that the state of the optical or microwave cavity can be directly measured by detecting the emitted photons. It is thus important to investigate how transport through a molecule is linked to the property of the emitted radiation [35,37].

In this paper we consider electronic transport through a single-level quantum dot, where the charge on the dot is coupled to the electric field of an electromagnetic cavity. We derive an expression for the current through the quantum dot taking into account the cavity dissipation $\kappa$, and arbitrary values of the coupling strength in the in-

![Figure 1. Schematic of two metallic electrodes forming a plasmonic nanocavity characterized by a resonating frequency $\omega_c/2\pi$ and damping rate $\kappa$. A single electronic level $\epsilon_0$ of a molecule in the nanogap couples to the electromagnetic radiation with coupling constant $\Lambda_m$. Electrons can tunnel to and from the dot with tunnelling rates $\Gamma_d$. Voltage drops, $V_d$, with respect to $\epsilon_0$ are indicated.](arXiv:1907.11269v1 [cond-mat.mes-hall] 25 Jul 2019)
coherent transport regime $\Gamma \ll k_B T$, with $\Gamma$ the electron tunnelling rate, $T$ the temperature, and $k_B$ the Boltzmann constant. Similarly to the Franck–Condon case, we find current steps at the inelastic thresholds for photon emission, but with a width controlled by $\kappa$ rather than $T$. We also derive the photon distribution and the second-order photon correlation function $g^{(2)}(t)$, where $t$ is the emission time. Its behaviour for $t = 0$ clearly shows that close to the first threshold for photon emission, for $\Gamma/\kappa \ll 1$, and $\Lambda_m \approx \omega_c$, photons anti-bunch: The junction becomes a single-photon source based on single-electron tunneling. For large bias voltages we find instead strong photon bunching with $g^{(2)}(0) \approx \kappa/\Gamma \gg 1$.

Model. Figure 1 shows a schematic of the system at hand. The Hamiltonian is written $H = H_S + H_I + H_B$, where

$$H_S = \hat{\varepsilon}_0 \hat{d}_1^\dagger \hat{d}_1 + \omega_c \hat{a}_1^\dagger \hat{a}_1 + \Lambda_m \hat{d}_1^\dagger \hat{d}_1 (\hat{a}_1^\dagger + \hat{a}_1),$$

with $\hat{d}^\dagger$ the creation operator for the electron on the dot single level of energy $\hat{\varepsilon}_0$, $\hat{a}^\dagger$ the creation operator for the photon field, and $\Lambda_m = \lambda \omega_c$ the coupling constant. We treat the electrons in the leads and the propagating electromagnetic modes as a bath: $H_B = \sum_{\alpha L/R} \sum_{\omega} \epsilon_{\alpha k} \hat{c}_{\alpha k}^\dagger \hat{c}_{\alpha k} + \sum_{\alpha k} \omega_q \hat{b}_q^\dagger \hat{b}_q$, where $\hat{c}_{\alpha k}^\dagger$ and $\hat{b}_q^\dagger$ are the creation operators for the electrons on the leads $\alpha = L, R$ with energy $\epsilon_{\alpha k}$ and for the propagating photons of energy $\omega_q$, respectively. The (linear) coupling to the bath is given by

$$H_I = \sum_{\alpha L/R} \sum_{\omega} [\hat{t}_{\alpha k} \hat{c}_{\alpha k}^\dagger \hat{b}_q + \hat{t}^\dagger_{\alpha k} \hat{c}_{\alpha k} \hat{b}_q^\dagger] + \sum_{\omega q} [\hat{t}_q \hat{d}_1^\dagger \hat{b}_q + \hat{t}_q^\dagger \hat{d}_1 \hat{b}_q^\dagger],$$

with $\hat{t}_{\alpha k}$ and $\hat{t}_q$ the tunnelling amplitudes. We first perform a standard Lang-Firsov unitary transformation on the Hamiltonian $\hat{H} = UHU^\dagger$, with $U = e^{\lambda \hat{d}_1^\dagger (\hat{a}_1^\dagger + \hat{a}_1)}$. This removes explicitly the electron-photon coupling term in $H_S$, shifts the dot-level energy $\hat{\varepsilon}_0 = \hat{\varepsilon}_0 - \lambda^2 m_0/\omega_0$ and modifies the $d$ operator in $H_I$ into $D = d e^{\lambda (\hat{a}_1^\dagger + \hat{a}_1)}$.

Master equation. Let us define the reduced density matrix $\rho(t)$ for the $d$ and $a$ degrees of freedom after tracing out the bath. We consider the relevant regime $\Gamma \ll k_B T \ll \omega_c$, where the dynamics of $\rho_d(t)$ can be described by the Born–Markov master equation:

$$\dot{\rho}(t) = \mathcal{L}\rho(t) = -i[\hat{H}_S, \rho(t)] + (\mathcal{L}_c + \mathcal{L}_e) \rho(t). \tag{2}$$

The first term contributing to the Liouvillian operator $\mathcal{L}$ gives the coherent evolution of $\rho(t)$. The second one describes the damping of the cavity mode

$$\mathcal{L}_c \rho(t) = \frac{\kappa}{2} \left[ \hat{a}_1^\dagger \hat{a}_1 \rho(t) - \hat{a}_1 \hat{a}_1^\dagger \rho(t) - \rho(t) \hat{a}_1 \hat{a}_1^\dagger \right] + \kappa B \left[ \hat{a}_1^\dagger \hat{a}_1 - 1 \right],$$

with $\kappa B = \lambda^2 m_0/\omega_0$, and $\kappa B = \lambda^2 m_0/\omega_0$.

Figure 2. (a) Electronic current $I$ versus the voltage drops $V_L$ and $V_R$ for $\lambda = 1.4$. (b) Current-voltage characteristics and (c) average photon occupation $\langle a_\pm \rangle$ in the cavity corresponding to the voltage profiles indicated in panel a (dashed and full lines) for different electron-photon coupling strengths $\lambda = 0.1$ (blue), $\lambda = 0.6$ (green) and $\lambda = 1.4$ (magenta). The model parameters are $\kappa = 10 k_B T = 1.0 \omega_c$ and $\Gamma_L = \Gamma_R = \Gamma / 2 = 10^{-3} \omega_c$. 

The last term describes incoherent electron tunneling $\mathcal{L}_e \rho(t) = \left[ \mathcal{D}_- \rho(t) - \rho(t) \mathcal{D}_+ \right] + \text{h.c.}$, where $\mathcal{D}_\pm = \int_{-\infty}^{\infty} d\omega \int_0^\infty dt \Gamma_\alpha(\omega) \langle \hat{a}_\alpha^\dagger(\omega) \rangle \hat{a}_\alpha(D_\pm(t) - t)$, and $\Gamma_\alpha = 2\pi \sum_k |t_{\alpha k}|^2 \delta(\omega - \epsilon_{\alpha k})$ is the tunneling rate from the lead $\alpha$, that in the usual wide-band approximation becomes $\omega$-independent. Finally, $D_1(-t)$ is the $D$ operator in the interaction representation with respect to $H_S$. We introduced the short-hand notation $f_\alpha^+ (\omega) = 1 - f_\alpha^- (\omega) = n_F(\omega - \mu_\alpha)$, with $\mu_\alpha$ the chemical potential of lead $\alpha$ and $n_F(\omega) = \{ e^{\omega/k_B T} + 1 \}^{-1}$ the Fermi distribution. The average or the correlation function of any observable $A, B$, can then be calculated in the stationary regime by $\langle A \rangle = \text{Tr}[A\rho^{st}]$ and $S_{AB}(t) = \langle A(t)B(0) \rangle = \text{Tr}[A e^{\mathcal{L}t} B\rho^{st}]$ with $\rho^{st}$ the stationary solution of Eq. 2.

Electronic current. Using the previous results, we derive the expression for the average electronic dc-current evaluated at lead $\alpha$

$$I_\alpha = \frac{e \Gamma_\alpha}{\pi} \Re \int_{-\infty}^{\infty} d\omega \left\{ f_\alpha^+(\omega) S_{DD1}(\omega) + f_\alpha^-(\omega) S_{D1D}(\omega) \right\} \tag{3}$$

$$f_\alpha^+(\omega) = 1 - f_\alpha^-(\omega) = n_F(\omega - \mu_\alpha),$$

where $\mu_\alpha$ the chemical potential of lead $\alpha$ and $n_F(\omega) = \{ e^{\omega/k_B T} + 1 \}^{-1}$ the Fermi distribution. The average or the correlation function of any observable $A, B$, can then be calculated in the stationary regime by $\langle A \rangle = \text{Tr}[A\rho^{st}]$ and $S_{AB}(t) = \langle A(t)B(0) \rangle = \text{Tr}[A e^{\mathcal{L}t} B\rho^{st}]$ with $\rho^{st}$ the stationary solution of Eq. 2.
where we introduced the Fourier transform of $f_{\pm}^\alpha$, $S_{DD^\dagger}$ and $S_{DI,D}$. Equation (3) enables to calculate the current in presence of strong damping rates $\kappa$, that for plasmonic cavities reaches low quality factors $\omega_c/\kappa \approx 10$ [26]. It allows to include the damping of the electromagnetic field during the tunnelling process. This expression and $\rho^{\alpha\dagger}$ can be evaluated numerically by projecting on the charge and harmonic oscillator basis.

Figure 2(a) reports the electronic current $I$ for strong coupling, $\lambda = 1.4$, as a function of the relative voltage drops $eV_{\alpha} = \mu_{\alpha} - \varepsilon_0$ between the chemical potential of lead $\alpha$ and the dot energy level [12]. Specific current-voltage characteristics, corresponding to symmetric ($V_L = -V_R$) and asymmetric ($eV_R = -0.2\omega_c$) voltage drops, are shown respectively as full and dashed lines in Fig. 2(b), for weak ($\lambda = 0.1$), moderate ($\lambda = 0.6$), and strong ($\lambda = 1.4$) coupling strengths. These exhibit similar features of the Franck-Condon blockade regime [30,32], with inelastic steps observed each time the voltage drop $eV_L = n\omega_c$ matches a multiple of the cavity-photon frequency. This is the threshold for one-electron tunnelling while emitting $n$ photons in the cavity.

The step heights are given by the Poisson distribution $P_n(\lambda) = e^{-\lambda^2}\lambda^{2n}/n!$, but in contrast to what is observed with vibron modes in molecular junctions [33, 34], the width of the steps is given by the cavity-losses $\kappa$, which exceed the temperature broadening.

**Emitted light.** We consider now the emitted light power $\sim \kappa\omega_c(a^\dagger a)$, by plotting the average population of the cavity mode in Fig. 2(c) as a function of $V_L$. We find that the photon population also increases with bias voltage in a step-like manner [35], correlated to the evolution of the electronic current [36], thus confirming that single-electron tunnelling is at the origin of light-emission inside the cavity. From Eq. 4, performing a secular approximation, we derive a rate equation for the photon population $P_n(t)$ [14]. A relevant experimental regime in plasmonic cavities is $\kappa \gg \Gamma$ and $\omega_c \gg k_BT$. Since the time between two tunnelling events is much longer than the damping time of the cavity, typically the circulating photon leaks out before a new photon is emitted in the cavity. In this limit $P_0 \approx 1$, and we find for the other populations $P_n = \Gamma_{0n}/n\kappa \ll 1$, with $\Gamma_{0n} = \sum_\alpha \Gamma_{\alpha}P_n(\lambda)n_F(n\omega_c - \mu_\alpha)$ the cavity 0 to $n$-photons transition rate induced by a single tunnelling event. The expression for $(a^\dagger a) = \sum_\alpha \Gamma_{0n}/\kappa$ describes then accurately the emitted power.

**Correlation function $g^{2}(t)$.** In order to characterize the statistics of the emitted light, we compute the second-order correlation function $g^{2}(t) = \langle a^\dagger a^\dagger(t)a(t)a\rangle/\langle a^\dagger a\rangle^2$ [38,42,47]. Let us begin with the $t = 0$ case, $g^{2}(0) = \langle \sum_n n(n-1)P_n\rangle/\langle \sum_n nP_n\rangle^2$. One can readily verify that in thermal equilibrium $g^{2}(0) = 2$. On Fig. 3 we show $g^{2}(0)$ as a function of $V_L$ and $V_R$, for three different values of $\lambda$. As expected, for $e|V_L - V_R| \ll k_BT$, one always finds the value of 2, corresponding to thermal equilibrium (pink regions on the diagonal $V_L = V_R$). Out of equilibrium we find either bunching $g^{2}(0) > 1$ or anti-bunching $g^{2}(0) < 1$. The anti-bunching appears for sufficiently strong coupling and is indicated by the blue regions with dashed border (where $g^{2}(0) = 1$).

In order to obtain an analytical expression for $g^{2}(0)$ we treat both the electron tunnelling and the thermal excitations as weak perturbation to $P_n = \delta_{n,0}$. For voltages $eV_L = -eV_R \leq 2\omega_c$ [14] we have

$$g^{2}(0) \approx \frac{\Delta[k\kappa\Gamma_{02} + (2\kappa\kappa + \Gamma_{12})(\kappa\kappa + \Gamma_{01} + \Gamma_{02})]}{(2(\kappa\kappa + \Gamma_{01} + \Gamma_{02})(2k\kappa + \Gamma_{12} + k\kappa + \Gamma_{02})^2}$$

with $\kappa\kappa = \kappa n_B(\omega_c)$, $\kappa\kappa = \kappa[1 + n_B(\omega_c)]$, $\Delta = (\kappa\kappa + \Gamma_{01} + \Gamma_{02})(2(k\kappa + \kappa\kappa + \Gamma_{12} + k\kappa + \Gamma_{02} + 2k\kappa + \Gamma_{02})$, and the rate $\Gamma_{12} = e^{-\lambda^2}\lambda^2(2 - \lambda^2)^2\sum_\alpha \Gamma_{\alpha}n_F(\omega_c - \mu_\alpha)/2$ for the transition from 1 to 2 photons in the cavity. Equation (4) agrees very well with the numerical calculations.
for $k_B T \geq 0.1 \omega_c$, (cf. thick lines in Fig. 1(a) and (b)). At lower temperature we thus show only the approximate Eq. (4), that does not suffer of numerical instability. In the strong coupling regime, Eq. (4) predicts a smooth crossover from the equilibrium value $g^{(2)}(0) = 2$ at low voltage, to an anti-bunching $g^{(2)}(0) < 1$ regime that appears close to the first inelastic threshold ($|eV_L| \approx \omega_c$ or $|eV_R| \approx \omega_c$). As temperature decreases the region of anti-bunching expands, eventually including almost the full bias range $[0, 2\omega_c]$, cf. Fig. 1(b).

Figure 4(c) shows the minimum value taken by $g^{(2)}(0)$ when minimized on the plane $(V_L, V_R)$ for a given value of the coupling $\lambda$. One finds that anti-bunching can be observed for $\lambda > 0.17$ for an asymmetric bias configuration, thus being at reach of present experiments. The case of symmetric bias is also shown, with anti-bunching beginning at $\lambda > 0.76$. Let us discuss now the anti-bunching mechanism for symmetric bias. When $P_{n+1} \ll P_n$, at lowest order $g^{(2)}(0) = 2P_2/P_1^2$. This expression gives 2 for thermal distribution $P_n \sim e^{-n\omega_c/k_B T}$. Anti-bunching is thus achieved for $2P_2 \ll P_1^2$. At very low temperature we can neglect $\kappa$, and the only way to populate the state 2 is either a 2-photon transition (for $eV_L > 2\omega_c$), or an electron-tunneling assisted transition from the state 1, controlled by $\Gamma_{12}$ (for $eV_L > \omega_c$). As a confirmation one finds that $P_1 \approx P_0 \Gamma_{01}/\kappa$ and $P_2 \approx P_1 \Gamma_{12}/2\kappa$, testifying that the result is just due to a balance between the light leaked out of the cavity and the photons emitted in the cavity by the tunnelling electrons. From the explicit expression of $\Gamma_{12}$ at low temperature ($k_B T \ll \omega_c$) one then finds that the minimum value of $g^{(2)}(0)$ is approximated by $(\lambda^2 - 2)^2/2$ [dotted line in Fig. 4(c)], tracing the $\lambda$-dependence of $\Gamma_{12}$. Its vanishing for $\lambda = \sqrt{2}$ is thus at the origin of the anti-bunching. A similar effect has also been recently reported in dc-biased Josephson junction coupled to microwave resonators [11, 12].

For larger voltages $eV_L \geq 2\omega_c$, we obtain analytically $g^{(2)}(0) \approx \kappa/2\Gamma$, as predicted by the numerical simulations giving a smooth evolution to strong bunching. This result agrees with the infinite bias voltage limit result recently reported in Ref. [15]. Finally, the time dependence of $g^{(2)}(t)$ as obtained by the numerical calculations shows a smooth crossover on a time scale $1/\kappa$ from $g^{(2)}(0) = 2$ to $g^{(2)}(\infty) = 1$ (uncorrelated photons) [16]. Only for $\lambda \approx 1$ we observe weak oscillations [44].

Conclusions. Charge fluctuations induced by electronic transport in a molecular single-electronic level are expected to couple strongly to the plasmonic mode formed by an STM tip and the substrate. We derived an expression for the current taking into account the strong damping of these cavities and obtained the current, emitted light intensity, and the correlation function $g^{(2)}(t)$. We showed that when the coupling strength is of the order $\lambda \sim 1$, Franck–Condon steps appear in both the current and the light intensity. Non-classical light can be emitted for a coupling strength in the range $0.17 < \lambda < 1.8$ for bias voltage near the one photon emission threshold. This prediction can be relevant for a series of experiments on STM cavities [13, 21]. An open question for future studies is to explore the interplay between the mono- and dipolar couplings and their respective roles in the luminescence properties of single molecules for which photon anti-bunching was reported [49]. Another interesting direction is the study of current response in presence of light irradiation of the plasmonic junction.

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[42] We plot the symmetrized current \( I = (I_L + I_R)/2 \), since for asymmetric bias voltages one observes in some cases weak non-conserving contributions.

[43] At this level of approximation, the steps of the cavity mode occupation appear to be broadened on the scale given by temperature instead of \( k \).


